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Supporting Information for

Asymmetric Fused Thiophenes for Field-Effect Transistors: Crystal Structure-Film Microstructure-Transistor Performance Correlations

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Compound	1	2	3	4	
Empirical formula	C20H7F5S3	C20H12S3	C28H9F5S6	C28H14S6	
Formula weight	438.44	348.48	632.71	542.75	
Temperature (K) ^b	100(2)	200(2)	296(2)	296(2)	
Crystal system	Monoclinic	Monoclinic	Triclinic	Monoclinic	
Space group	P21/c	P21/c	P-1	P2(1)/c	
	a = 5.8734(2)	a = 7.468(4)	a = 3.8338(5)	a = 5.9639(18)	
	$\alpha = 90^{\circ}$	$\alpha = 90^{\circ}$	$\alpha = 86.15(1)^{\circ}$	$\alpha = 90^{\circ}$	
Unit cell dimensions	b = 36.1226(12)	b = 5.916(3)	b = 5.8334(8)	b = 7.509(2)	
(Å)	β=91.677 (2)°	$\beta = 94.01(4)^{\circ}$ $\beta = 87.92(1)^{\circ}$		$\beta = 92.83(1)^{\circ}$	
	c = 7.4967(2)	c = 34.719(15)	c = 26.039(4)	c = 50.362(15)	
	$\gamma = 90^{\circ}$	$\gamma = 90^{\circ}$	$\gamma = 87.04(1)^{\circ}$	$\gamma = 90^{\circ}$	
<i>V</i> , Å ³	1589.85(9)	1530.15(449)	579.93(49)	2252.61(137)	
Z	4	4	1	4	
d (calc), g/cm3	1.832	1.5126 1.81154		1.60028	
Absorption	0.525	0.470	0.651	0.626	
coefficient (mm ⁻¹)	0.323	0.479	0.031	0.020	
F(000)	880	720	318	1112	
R _{All}	0.1794	0.2708	0.1096	0.2014	
Crystal size (mm)	$0.44 \times 0.20 \times 0.04$	0.60 x 0.46 x 0.01	0.33 x 0.14 x 0.01	0.28 x 0.19 x 0.01	
Reflections collected	30972	8859	4776	12233	
Independent	3658	2642	2031	3592	
reflections	5050	2042	2001		
R _{int}	0.0554	0.1837	0.0598	0.1507	
Final R indices	R1 = 0.0648	R1 = 0.1599	R1 = 0.0692	R1 = 0.0698	
[I>2sigma(I)] ^c	wR2 = 0.17	wR2 = 0.3548	wR2 = 0.1767	wR2 = 0.1613	
R indices (all data)	R1 = 0.0706	R1 = 0.2708	R1 = 0.1096	R1 = 0.2014	
ix mulces (all uala)	wR2 = 0.1789	wR2 = 0.4062	wR2 = 0.2001	wR2 = 0.2479	

 Table S1. Summary of Crystal Structure Data for compounds 1-4.^a

^a CCD area detector diffractometer; Mo K α radiation; $\lambda = 0.71073$ Å. ^b Temperature for data collection. ^c Refinement method: Full-matrix least-squares on F2.

Table	S2.	Centroid-to-centroid	distance	(L)	in	the	crystal	strucutures,	calculated
reorgar	nizati	on energies (λ^+) , electro	onic coupl	ings	$(t^{+}),$	and	mobilitie	es (μ^+) for hole	e transport.





Figure S1. AFM images (5 × 5 μ m²) of films (50 nm) of FPP-BDTT (3) and DP-BDTT (4) on various substrates.



Figure S2. X-ray Diffraction pattern of thin films of FPP-DTT (1) and DP-DTT (2) on various substrates.